

L Number	Hits	Search Text	DB	Time stamp
365	0	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)and 204-205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 09:25
367	0	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)and 205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:02
366	13	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)and 204/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 09:26
371	366	204/192.29	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:02
372	605	204/192.35	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:02
373	346	205/223	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:02
376	0	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)and 205/223	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:03
375	1	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)and 204/192.35	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:03
374	4	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)and 204/192.29	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/15 10:03
-	1151	349/143	USPAT; US-PGPUB; JPO	2003/03/07 14:47
-	664	349/187	USPAT; US-PGPUB; JPO	2003/03/06 13:17
-	1050	349/43	USPAT; US-PGPUB; JPO	2004/07/14 09:26
-	2141	pixel with temperature	USPAT; US-PGPUB; JPO	2003/03/06 13:20
-	86	(pixel with temperature) and (pixel with amorphous) and (inject\$4 near\$5 hydroben near\$5 gas)	USPAT; US-PGPUB; JPO	2003/03/06 13:23
-	0	(pixel with temperature) and (pixel with amorphous) and (inject\$4 near\$5 hydroben near\$5 gas) and (etch\$4 with (weak adj acide))	USPAT; US-PGPUB; JPO	2003/03/06 13:24
-	0	(pixel with temperature) and (pixel with amorphous) and (inject\$4 near\$5 hydroben near\$5 gas) and etch\$4 and 349/143	USPAT; US-PGPUB; JPO	2003/03/06 13:24
-	28	(pixel with temperature) and 349/143	USPAT; US-PGPUB; JPO	2003/03/06 13:26

-	61	(pixel with amorphous) and 349/143	USPAT; US-PGPUB; JPO	2003/03/06 13:26
-	180	(pixel with amorphous) and 349/43	USPAT; US-PGPUB; JPO	2003/03/06 13:26
-	107	(pixel with temperature) and (pixel with amorphous)	USPAT; US-PGPUB; JPO	2003/03/06 14:24
-	5558	(pixel and temperature and amorphous)	USPAT; US-PGPUB; JPO	2003/03/06 13:33
-	3907	(pixel and temperature and amorphous) and (inject\$4 near\$5 (hydrogen with gas))	USPAT; US-PGPUB; JPO	2003/03/06 13:34
-	768	(pixel and temperature and amorphous) and (inject\$4 near\$5 (hydrogen with gas)) and 349\$.ccls.	USPAT; US-PGPUB; JPO	2003/03/06 13:35
-	2855	(pixel and temperature and amorphous) and (inject\$4 near\$5 (hydrogen with gas)) and (liquid adj crystal) and substrate	USPAT; US-PGPUB; JPO	2003/03/06 13:36
-	7	(pixel and temperature and amorphous) and (inject\$4 near\$5 (hydrogen with gas)) and (liquid adj crystal) and substrate and (etch\$4 with (weak adj acid))	USPAT; US-PGPUB; JPO	2003/03/06 16:39
-	111	(pixel with temperature) and (pixel with amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:09
-	7	(pixel and temperature and amorphous) and (inject\$4 near\$5 (hydrogen with gas)) and (liquid adj crystal) and substrate and (etch\$4 with (weak adj acid))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/06 16:41
-	1	5135581.pn.	USPAT; US-PGPUB; JPO	2004/02/20 10:48
-	97	(pixel with amorphous) and 349/43 and temperature	USPAT; US-PGPUB; JPO	2003/03/07 15:29
-	29	(pixel with amorphous) and 349/187	USPAT; US-PGPUB; JPO	2003/03/07 16:34
-	62	(pixel with temperature) and 349/43	USPAT; US-PGPUB; JPO	2003/03/07 16:50
-	27	(pixel with temperature) and 349/187	USPAT; US-PGPUB; JPO	2003/03/07 16:51
-	54	(pixel with temperature) and (pixel with amorphous) and (inject\$4 near\$5 hydroben near\$5 gas) and etch\$4	USPAT; US-PGPUB; JPO	2003/10/17 16:57
-	7	(pixel with temperature) and (pixel with amorphous) and (inject\$4 near\$5 hydroben near\$5 gas) and etch\$4 and (vacuum adj chamber)	USPAT; US-PGPUB; JPO	2003/10/17 16:59
-	12	(pixel with temperature) and (pixel with amorphous) and (vacuum adj chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/17 17:10
-	1	20020085168.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 09:07
-	1	5135581.pn.	USPAT	2004/02/20 09:22
-	1	6433842.pn.	USPAT	2004/02/20 09:35
-	293	349/43 and passivation and (contact adj hole) near10 (drain adj electrode)	USPAT; US-PGPUB; JPO	2004/07/14 09:28
-	287	349/43 and passivation and (contact adj hole) near10 (drain adj electrode)and pixel	USPAT; US-PGPUB; JPO	2004/07/14 09:28

-	245	349/43 and passivation and (contact adj hole) near10 (drain adj electrode) and (pixel near10 (contact adj hole))	USPAT; US-PGPUB; JPO	2004/07/14 09:56
-	0	349/43 and passivation and (contact adj hole) near10 (drain adj electrode) and (pixel near10 (contact adj hole)near10 (vacuum adj chamber))	USPAT; US-PGPUB; JPO	2004/07/14 09:59
-	1	passivation and (contact adj hole) near10 (drain adj electrode) and (pixel near10 (contact adj hole)near10 (vacuum adj chamber))	USPAT; US-PGPUB; JPO	2004/07/14 10:00
-	2	passivation and (contact adj hole) near10 (drain adj electrode) and (pixel near10(vacuum adj chamber))	USPAT; US-PGPUB; JPO	2004/07/14 10:13
-	726	((pixel or conduct\$4) near10 (vacuum adj chamber))and sputter\$4	USPAT; US-PGPUB; JPO	2004/07/14 10:23
-	25	((pixel or conduct\$4) near10 (vacuum adj chamber))and (sputter\$4 near10 hydrogen)	USPAT; US-PGPUB; JPO	2004/07/14 11:39
-	130144	substrate near10 temperature	USPAT; US-PGPUB; JPO	2004/07/14 11:40
-	34959	(substrate near10 temperature) and sputter\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/14 11:41
-	4237	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/14 11:41
-	2358	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/14 11:42
-	262	(substrate near10 temperature) and sputter\$4 and (pixel or cinduct\$4) and hydrogen and (vacuum adj chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/07/15 09:25